



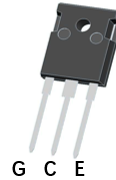
JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

## CGWT80N65F2SAD

### CGWT80N65F2SAD

| $V_{CE}$ | $I_C$ ( $T_C=100^{\circ}C$ ) | $V_{CE(sat)}$ |
|----------|------------------------------|---------------|
| 650V     | 80A                          | 1.55V         |

#### TO-247



### DESCRIPTION

The CGWT80N65F2SAD is used JSCJ's second generation IGBT technology, has advanced Trench and FS(Field Stop) Structure, it's with high application frequent, low Collector-Emitter Saturation Voltage and switching loss, can easy to use in parallel.

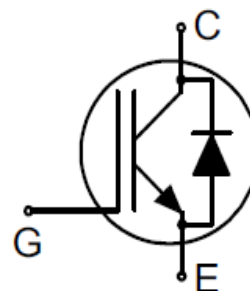
### Features

- 650V breakdown Voltage
- Low  $V_{ce(sat)}$  and positive temperature coefficient
- High speed switching, Low switching loss
- With fast and soft recovery freewheeling diode
- Good EMI behavior

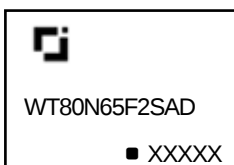
### Application

- UPS & PFC applications
- Solar Inverter
- EV Charger
- Power Storage
- Welder

### EQUIVALENT CIRCUIT



### MARKING



WT80N65F2SAD = Device code  
Solid dot = Green molding compound device, if none, the normal device  
XXXX = Code

| Order Code     | Package | Marking      | Parking |
|----------------|---------|--------------|---------|
| CGWT80N65F2SAD | TO-247  | WT80N65F2SAD | Tube    |



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## IGBT Discrets & Modules

感谢您的支持，如需要完整规格书，请联系：<[igbt.list@jscj-elec.com](mailto:igbt.list@jscj-elec.com)>，谢谢！

Thank you for your support. If you need a complete **datasheet**, please contact:

<[igbt.list@jscj-elec.com](mailto:igbt.list@jscj-elec.com)>. Thank you!